

**METHOD FOR MAKING GROUP III NITRIDE
DEVICES AND DEVICES PRODUCED THEREBY**

Abstract of the Disclosure

A method is for making at least one semiconductor device including providing a sacrificial growth substrate of Lithium Aluminate (LiAlO_2); forming at least one semiconductor layer including a Group III nitride adjacent the sacrificial growth substrate; attaching a mounting substrate adjacent the at least one semiconductor layer opposite the sacrificial growth substrate; and removing the sacrificial growth substrate. The method may further include adding at least one contact onto a surface of the at least one semiconductor layer opposite the mounting substrate, and dividing the mounting substrate and at least one semiconductor layer into a plurality of individual semiconductor devices. To make the final devices, the method may further include bonding the mounting substrate of each individual semiconductor device to a heat sink. The step of removing the sacrificial substrate may include wet etching the sacrificial growth substrate.